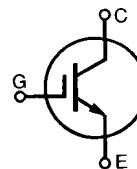


HiPerFAST™ IGBT Lightspeed™ Series

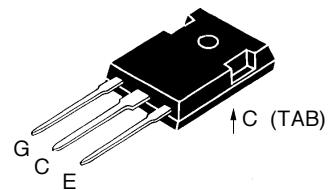
IXGH 12N60C



V_{CES} = 600 V
 I_{C25} = 24 A
 $V_{CE(sat)}$ = 2.7 V
 $t_{fi(typ)}$ = 55 ns

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	24	A
I_{C90}	$T_C = 90^\circ\text{C}$	12	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	48	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 33 \Omega$ Clamped inductive load, $L = 300 \mu\text{H}$	$I_{CM} = 24$ @ 0.8 V_{CES}	A
P_c	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{sig}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 0.55/5	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- Very high frequency IGBT
- New generation HDMOS™ process
- International standard package JEDEC TO-247
- High peak current handling capability

Applications

- PFC circuit
- AC motor speed control
- DC servo and robot drives
- Switch-mode and resonant-mode power supplies
- High power audio amplifiers

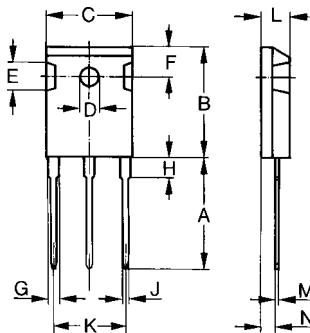
Advantages

- Fast switching speed
- High power density

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{GE} = V_{GE}$	2.5	5.0	V
I_{CES}	$V_{CE} = 0.8 V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	200 1.5	μA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$		± 100	nA
$V_{CE(sat)}$	$I_C = I_{CE90}$, $V_{GE} = 15 \text{ V}$	2.1	2.7	V

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$	5	11	S	
C_{ies} C_{oes} C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	860		pF	
		64		pF	
		15		pF	
Q_g Q_{ge} Q_{gc}	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $V_{CE} = 0.5 V_{CES}$	32		nC	
		10		nC	
		10		nC	
$t_{d(on)}$ t_{ri} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $L = 300 \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 18 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G	20		ns	
		20		ns	
		60		ns	
		55		ns	
		0.09		mJ	
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$, $L = 300 \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 18 \Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G	20		ns	
		20		ns	
		0.15		mJ	
		85	180	ns	
		85	180	ns	
		0.27	0.60	mJ	
R_{thJC}			1.25	K/W	
R_{thCK}		0.25		K/W	

TO-247 AD (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,237,481 5,486,715 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,381,025